L Number		Search Text	DB	Time stamp
1	19	block adj mold\$3 and semiconductor and clean\$3	USPAT	2003/01/06 10:50
2	0	mold\$3 and semiconductor near4 clean\$3	USPAT	2003/01/06 12:57
3	1	<pre>same rie same roughen\$ mold\$3 and semiconductor near4 clean\$3</pre>	USPAT	2003/01/06 11:05
3		same plasma same roughen\$	USPAT	2003/01/06 11:29
4	0	mold\$3 and semiconductor same substrate near4 clean\$3 same plasma same roughen\$	USPAI	2003/01/00 11.27
5	27	mold\$3 and semiconductor same substrate	USPAT	2003/01/06 12:49
	0	near4 clean\$3 same plasma "6200121" and fr4	USPAT	2003/01/06 14:15
6	_	mold\$4 same fr4	USPAT	2003/01/06 12:51
8	0	mold\$3 and fr4 same semiconductor near4 clean\$3	USPAT	2003/01/06 13:01
9	69	mold\$3 and fr4 same semiconductor	USPAT	2003/01/06 13:01
10		"6200121" and clean\$	USPAT	2003/01/06 14:15
11		"6200121" and clean\$4	USPAT	2003/01/06 14:50
14	30	multiple same stack\$3 same chips same encapsulat\$4	USPAT	2003/01/06 14:54